

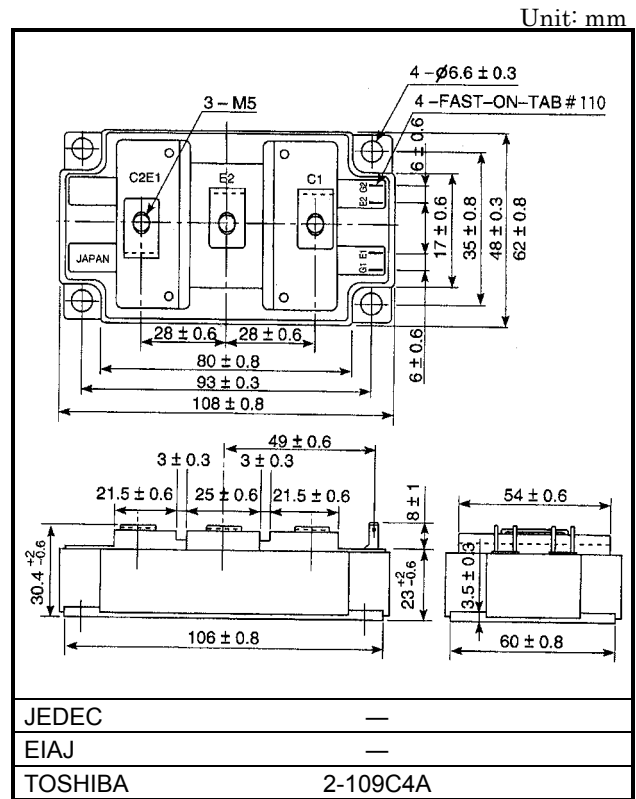
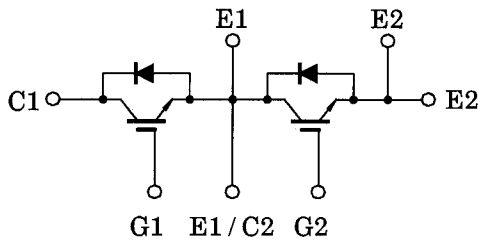
TOSHIBA GTR Module Silicon N Channel IGBT

MG100Q2YS51

High Power Switching Applications
Motor Control Applications

- High input impedance
- High speed : $t_f = 0.3\mu s$ (Max)
@Inductive load
- Low saturation voltage
: $V_{CE(sat)} = 3.6V$ (Max)
- Enhancement-mode
- Includes a complete half bridge in one package.
- The electrodes are isolated from case.

Equivalent Circuit



Weight: 430g

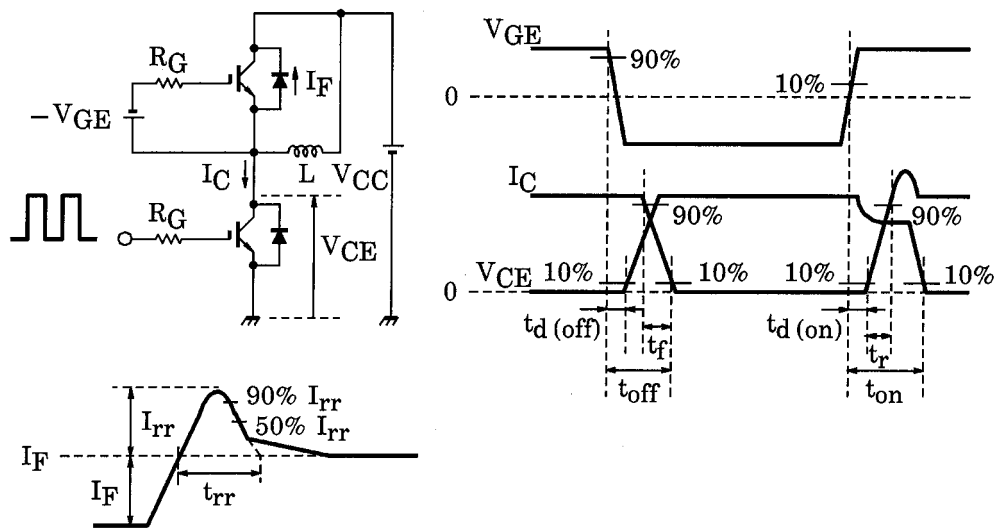
Maximum Ratings (Ta = 25°C)

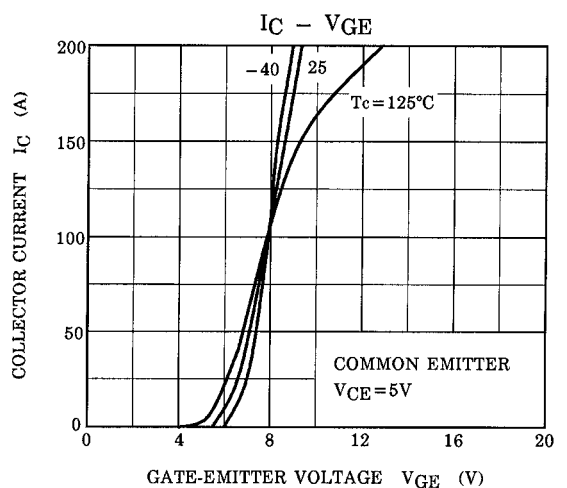
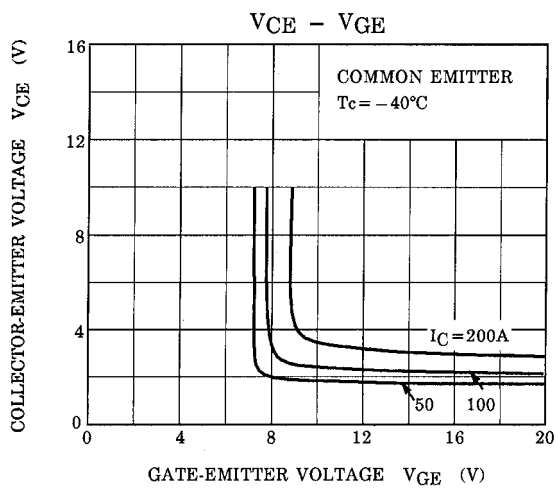
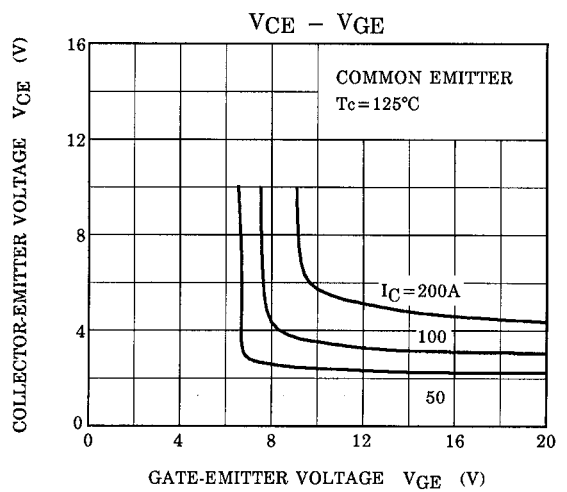
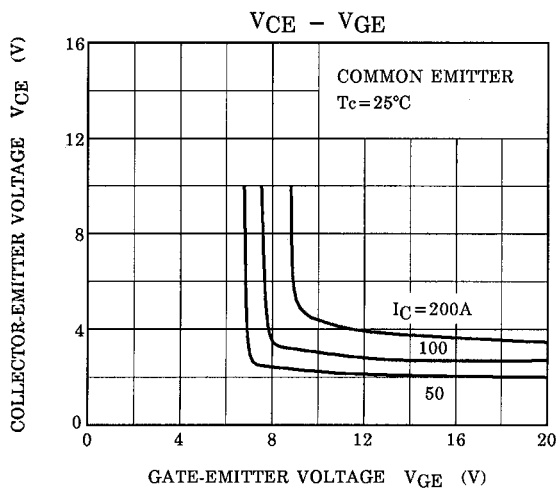
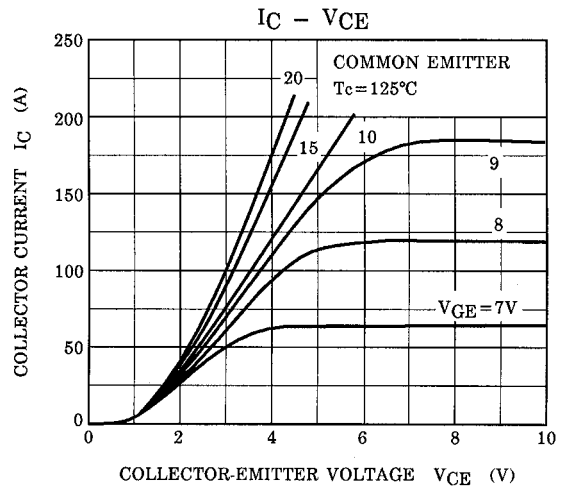
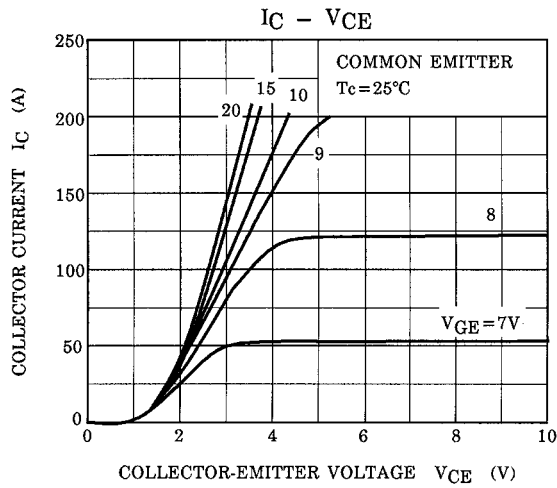
Characteristic	Symbol	Rating	Unit	
Collector-emitter voltage	V_{CES}	1200	V	
Gate-emitter voltage	V_{GES}	±20	V	
Collector current	DC	I_C (25°C / 80°C)	150 / 100	A
	1ms	I_{CP} (25°C / 80°C)	300 / 200	
Forward current	DC	I_F	100	A
	1ms	I_{FM}	200	
Collector power dissipation (Tc = 25°C)	P_C	660	W	
Junction temperature	T_j	150	°C	
Storage temperature range	T_{stg}	-40 ~ 125	°C	
Isolation voltage	V_{Isol}	2500 (AC 1 min.)	V	
Screw torque (Terminal / mounting)	—	3 / 3	N·m	

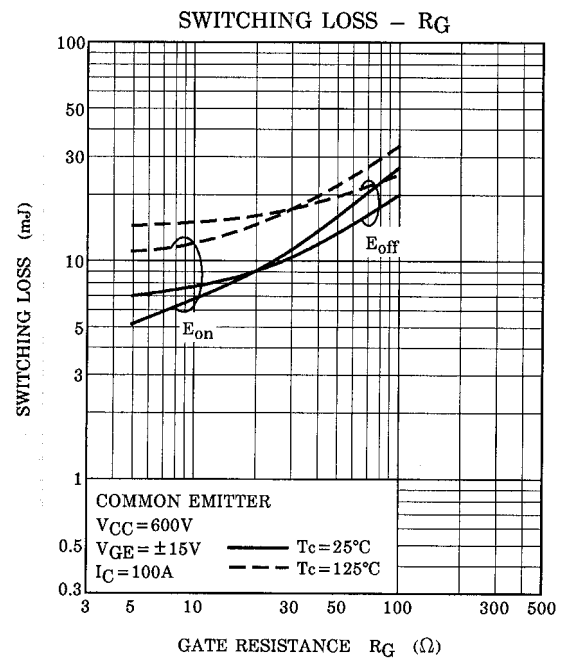
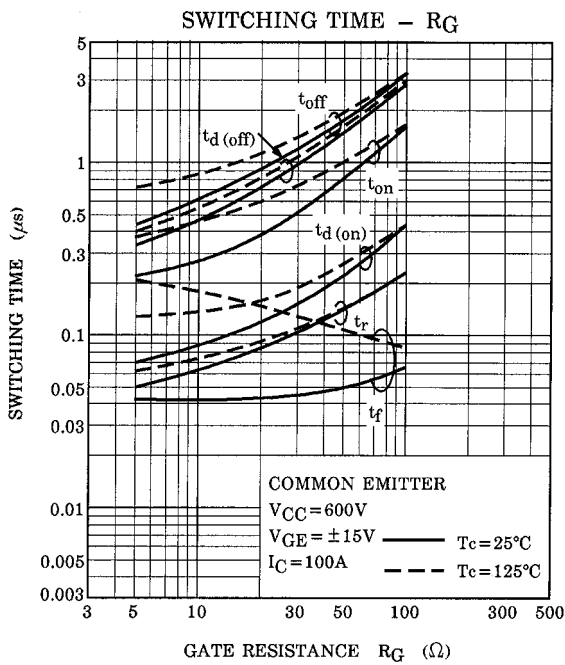
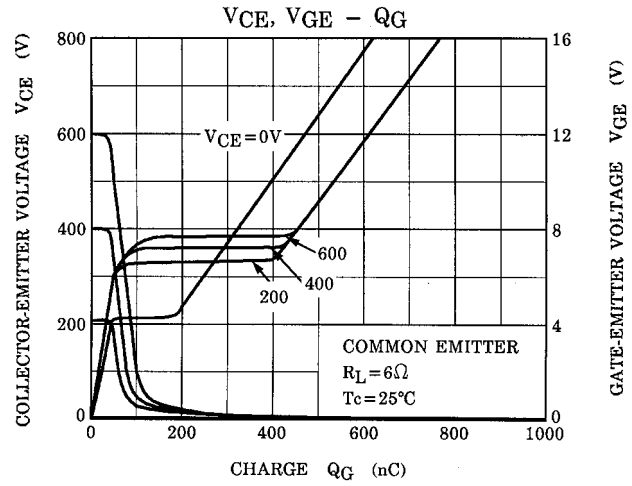
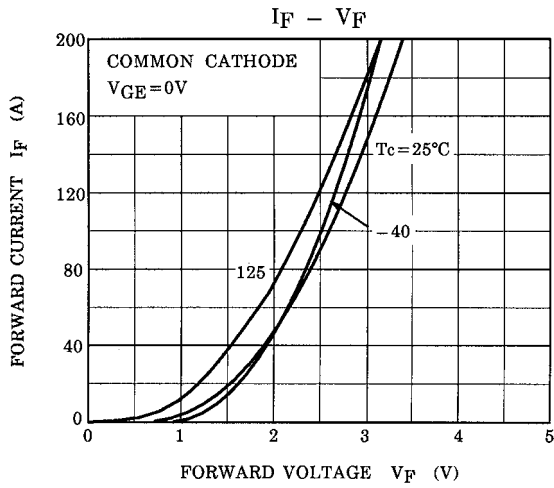
Electrical Characteristics (Ta = 25°C)

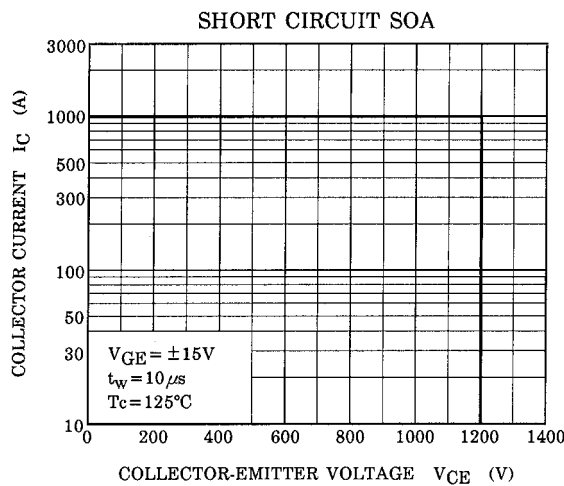
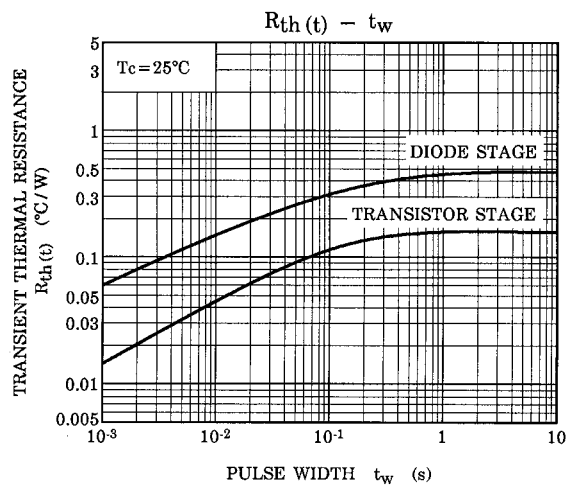
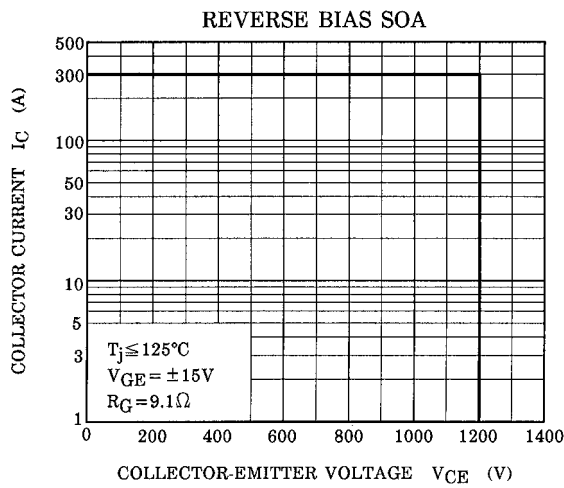
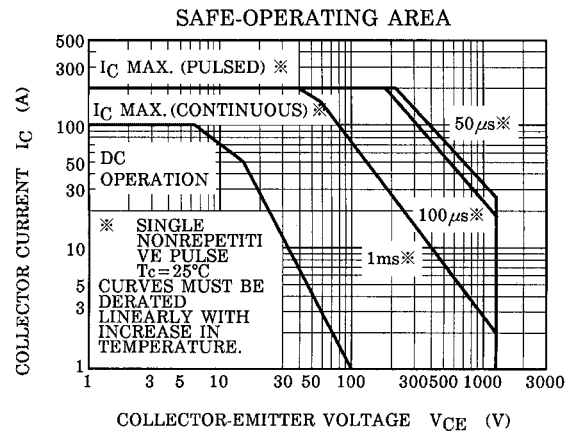
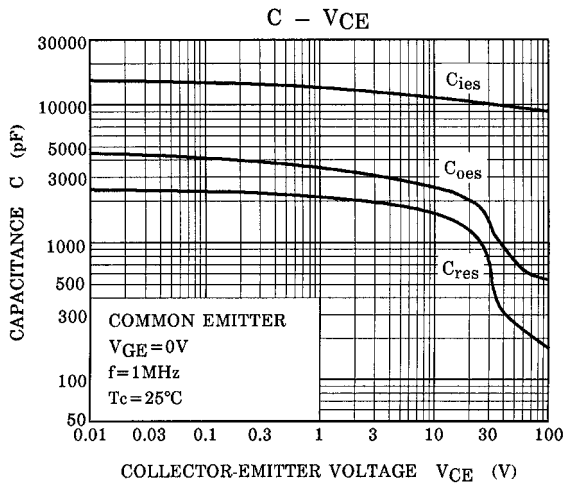
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate leakage current	I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 500	nA	
Collector cut-off current	I_{CES}	$V_{CE} = 1200V, V_{GE} = 0$	—	—	2.0	mA	
Gate-emitter cut-off voltage	$V_{GE (off)}$	$I_C = 100mA, V_{CE} = 5A$	3.0	—	6.0	V	
Collector-emitter Saturation voltage	$V_{CE (sat)}$	$I_C = 100A, V_{GE} = 15V$	$T_j = 25^\circ C$	—	2.8	3.6	V
			$T_j = 125^\circ C$	—	3.1	4.0	
Input capacitance	C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	12.0	—	nF	
Switching time	Turn-on delay time	$t_{d(on)}$	—	0.05	—	μs	
	Rise time	t_r	Inductive load $V_{CC} = 600V$ $I_C = 100A$ $V_{GE} = \pm 15V$ $R_G = 9.1\Omega$ (Note 1)	—	0.05		—
	Turn-on time	t_{on}		—	0.2		—
	Turn-off delay time	$t_{d(off)}$		—	0.5		—
	Fall time	t_f		—	0.1		0.3
	Turn-off time	t_{off}		—	0.6		—
Forward voltage	V_F	$I_F = 100A, V_{GE} = 0$		—	2.4	3.5	V
Reverse recovery time	t_{rr}	$I_F = 100A, V_{GE} = -10V$ $di / dt = 700A / \mu s$ (Note 1)	—	0.1	0.25	μs	
Thermal resistance	$R_{th (j-c)}$	Transistor stage	—	—	0.16	$^\circ C / W$	
		Diode stage	—	—	0.47		

Note 1: Switching time and reverse recovery time test circuit & timing chart









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